



April 2000

QFET™

# FQB7N30 / FQI7N30

## 300V N-Channel MOSFET

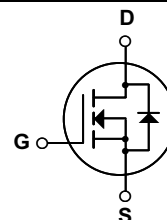
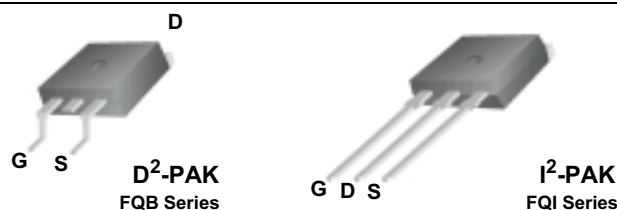
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supply.

### Features

- 7A, 300V,  $R_{DS(on)} = 0.7\Omega$  @  $V_{GS} = 10V$
- Low gate charge ( typical 13 nC)
- Low  $C_{rss}$  ( typical 12 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQB7N30 / FQI7N30	Units
$V_{DSS}$	Drain-Source Voltage	300	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )	7.0	A
	- Continuous ( $T_C = 100^\circ\text{C}$ )	4.43	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	28	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	380	mJ
$I_{AR}$	Avalanche Current (Note 1)	7.0	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	8.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
$P_D$	Power Dissipation ( $T_A = 25^\circ\text{C}$ ) *	3.13	W
	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	85	W
	- Derate above $25^\circ\text{C}$	0.68	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.47	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	40	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C}/\text{W}$

\* When mounted on the minimum pad size recommended (PCB Mount)

**Electrical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	300	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.3	--	$V/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 300\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 240\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3.5\text{ A}$	--	0.53	0.7	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 3.5\text{ A}$ (Note 4)	--	4.3	--	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	470	610	pF
$C_{oss}$	Output Capacitance		--	100	130	pF
$C_{rss}$	Reverse Transfer Capacitance		--	12	16	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 150\text{ V}, I_D = 7.0\text{ A},$ $R_G = 25\text{ }\Omega$  (Note 4, 5)	--	13	35	ns
$t_r$	Turn-On Rise Time		--	75	160	ns
$t_{d(off)}$	Turn-Off Delay Time		--	25	60	ns
$t_f$	Turn-Off Fall Time		--	35	80	ns
$Q_g$	Total Gate Charge	$V_{DS} = 240\text{ V}, I_D = 7.0\text{ A},$ $V_{GS} = 10\text{ V}$  (Note 4, 5)	--	13	17	nC
$Q_{gs}$	Gate-Source Charge		--	3.4	--	nC
$Q_{gd}$	Gate-Drain Charge		--	6.4	--	nC

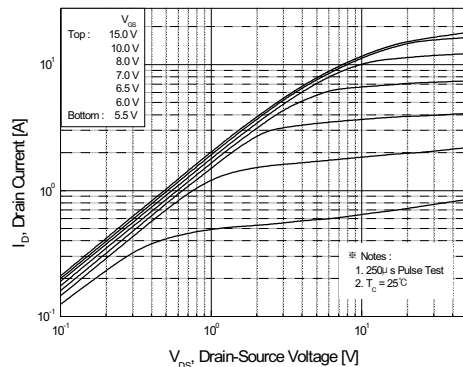
**Drain-Source Diode Characteristics and Maximum Ratings**

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	7.0	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	28	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 7.0 A	--	--	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 7.0 A, dI <sub>F</sub> / dt = 100 A/μs (Note 4)	--	150	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	0.74	--	μC

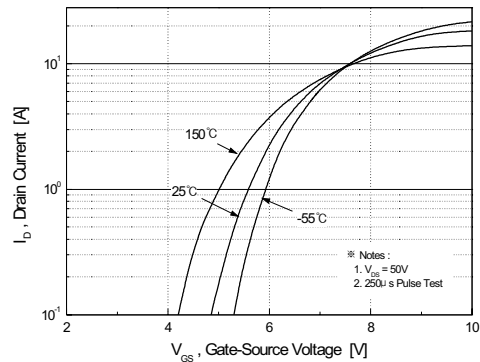
**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 12.9\text{ mH}, I_{AS} = 7.0\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 7.0\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

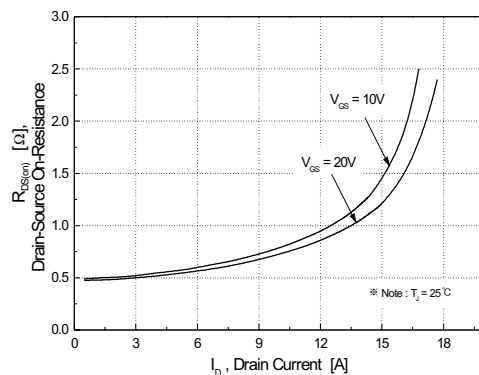
# Typical Characteristics



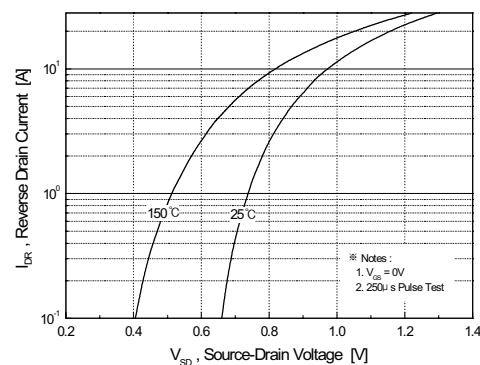
**Figure 1. On-Region Characteristics**



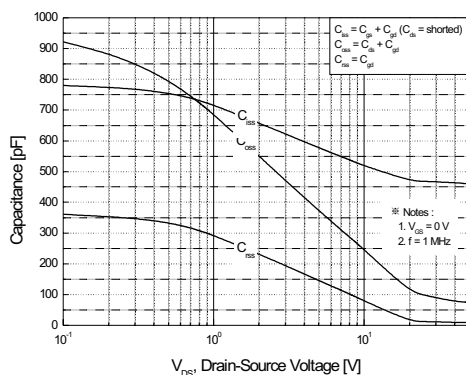
**Figure 2. Transfer Characteristics**



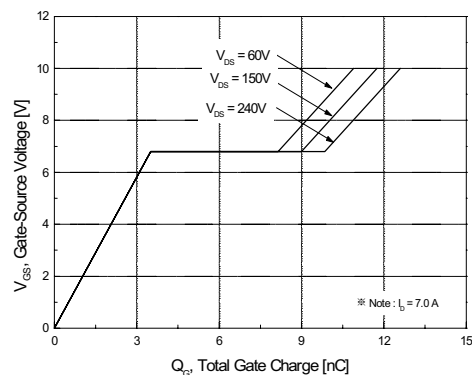
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**

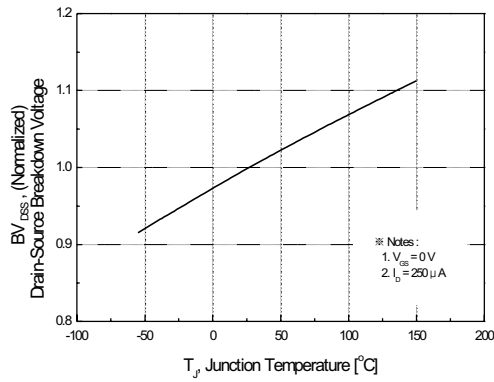


**Figure 5. Capacitance Characteristics**

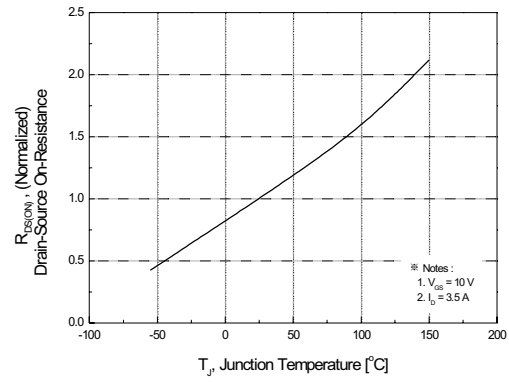


**Figure 6. Gate Charge Characteristics**

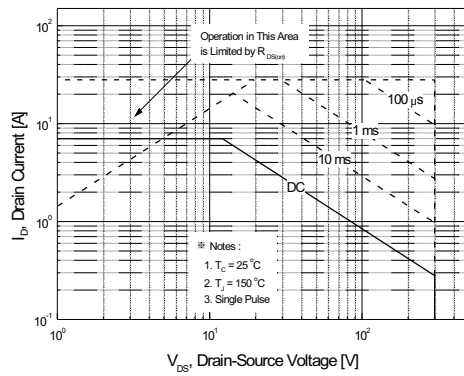
## Typical Characteristics (Continued)



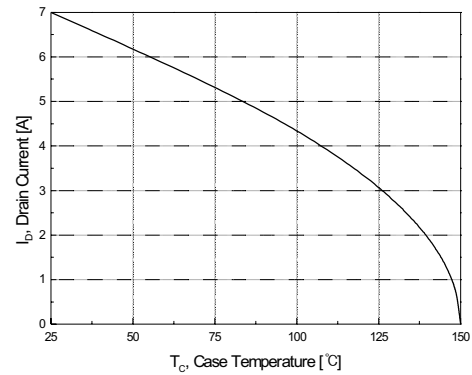
**Figure 7. Breakdown Voltage Variation vs. Temperature**



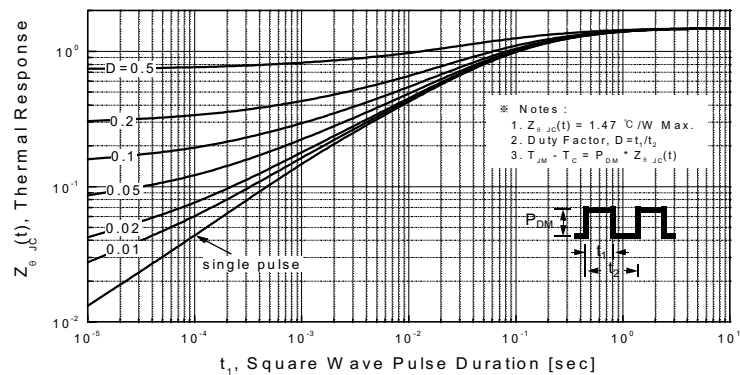
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**

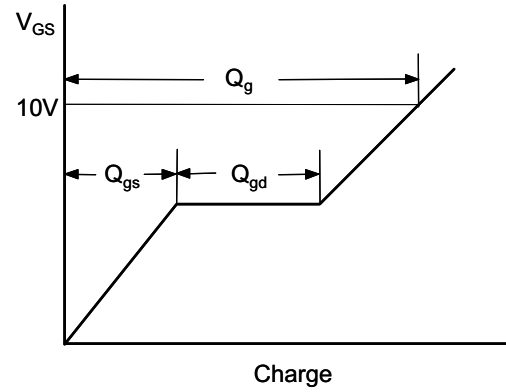
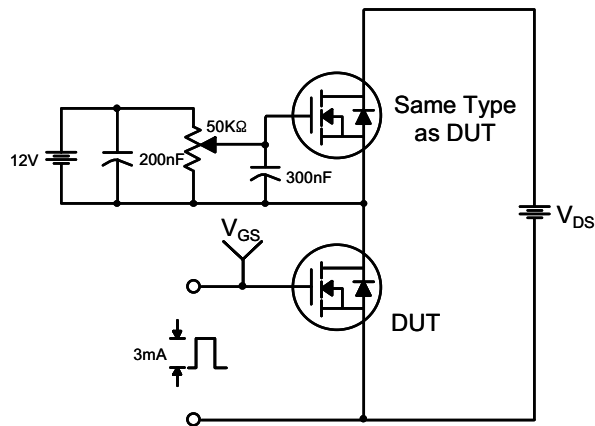


**Figure 10. Maximum Drain Current vs. Case Temperature**

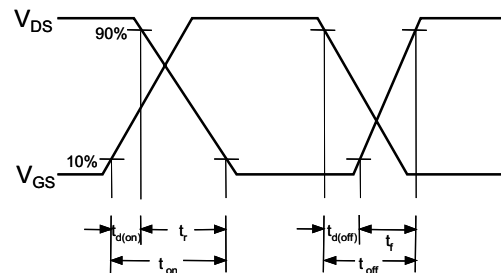
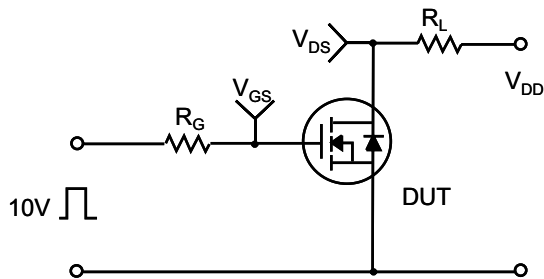


**Figure 11. Transient Thermal Response Curve**

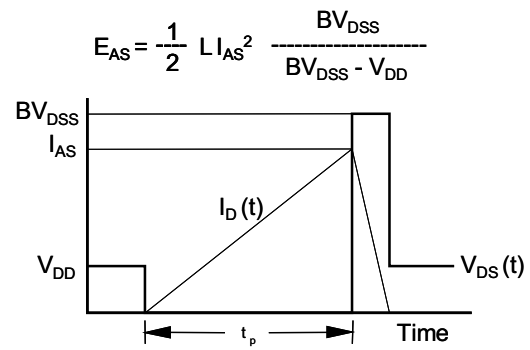
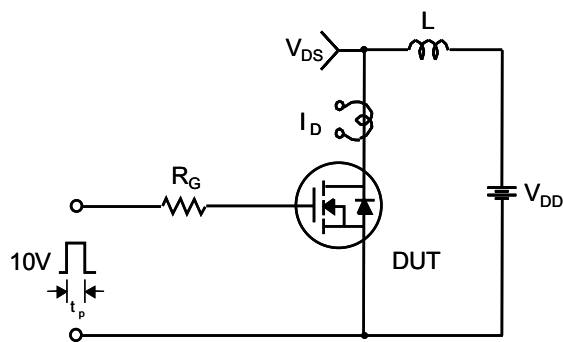
### Gate Charge Test Circuit & Waveform



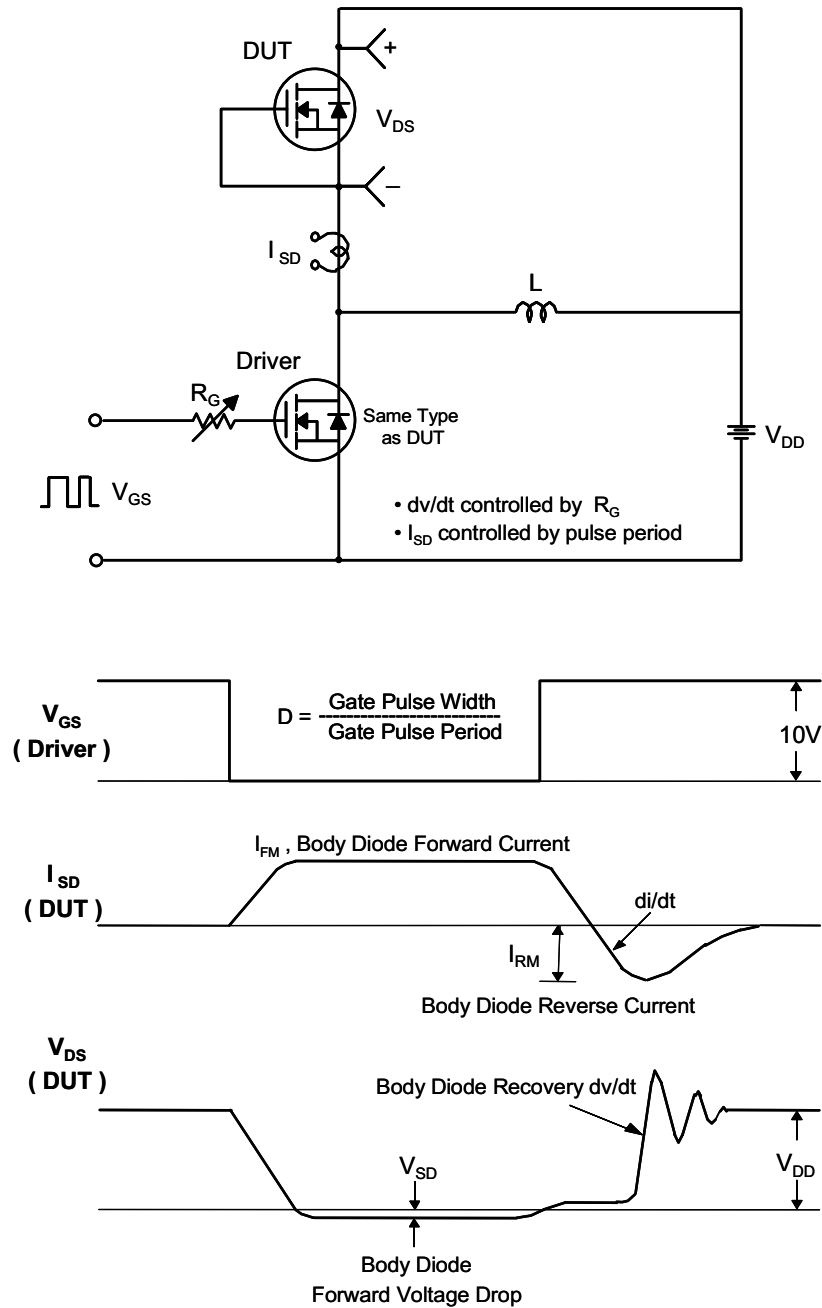
### Resistive Switching Test Circuit & Waveforms



### Unclamped Inductive Switching Test Circuit & Waveforms



# Peak Diode Recovery dv/dt Test Circuit & Waveforms



Technical drawing of a 10-pin D-sub connector, showing three views: front, side, and top. Dimensions are in millimeters.

**Front View (Top Left):**

- Overall width:  $9.90 \pm 0.20$
- Overall height:  $15.30 \pm 0.30$
- Pin height (from base):  $4.90 \pm 0.20$
- Pin pitch:  $2.54$  TYP
- Pin diameter:  $0.80 \pm 0.10$
- Pin length (from base):  $1.27 \pm 0.10$
- Pin spacing (from center):  $1.40 \pm 0.20$
- Pin diameter (from center):  $1.20 \pm 0.20$
- Pin diameter (from center):  $9.20 \pm 0.20$
- Pin diameter (from center):  $1.20 \pm 0.20$
- Pin diameter (from center):  $0.40$

**Side View (Top Right):**

- Overall width:  $4.50 \pm 0.20$
- Overall height:  $2.54 \pm 0.30$
- Pin height (from base):  $2.00 \pm 0.10$
- Pin pitch:  $2.54$  TYP
- Pin diameter:  $0.80 \pm 0.10$
- Pin length (from base):  $1.27 \pm 0.10$
- Pin spacing (from center):  $1.40 \pm 0.20$
- Pin diameter (from center):  $1.20 \pm 0.20$
- Pin diameter (from center):  $9.20 \pm 0.20$
- Pin diameter (from center):  $1.20 \pm 0.20$
- Pin diameter (from center):  $0.40$

**Top View (Bottom Left):**

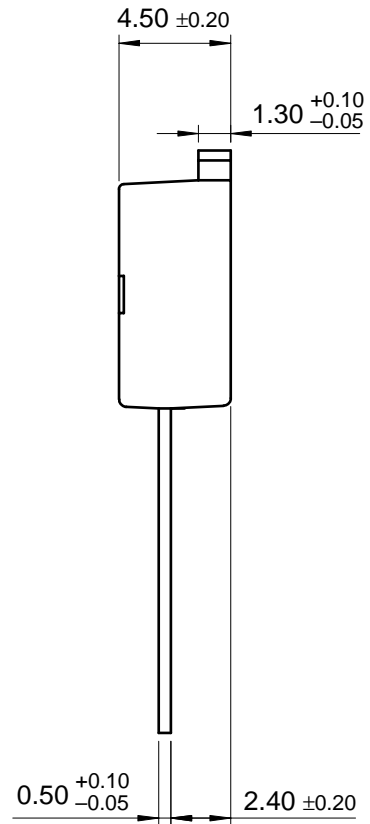
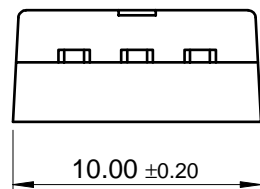
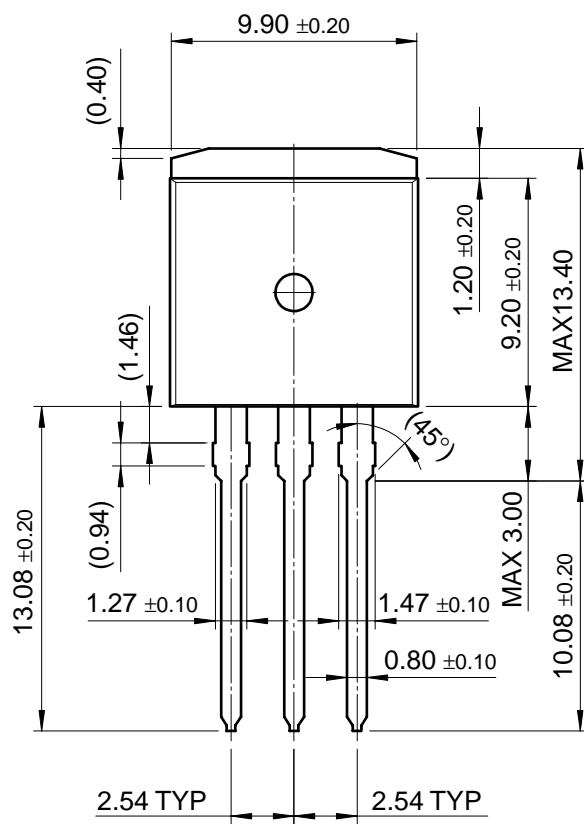
- Overall width:  $10.00 \pm 0.20$
- Overall height:  $15.30 \pm 0.30$
- Pin height (from base):  $4.90 \pm 0.20$
- Pin pitch:  $2.54$  TYP
- Pin diameter:  $0.80 \pm 0.10$
- Pin length (from base):  $1.27 \pm 0.10$
- Pin spacing (from center):  $1.40 \pm 0.20$
- Pin diameter (from center):  $1.20 \pm 0.20$
- Pin diameter (from center):  $9.20 \pm 0.20$
- Pin diameter (from center):  $1.20 \pm 0.20$
- Pin diameter (from center):  $0.40$

**Bottom View (Bottom Right):**

- Overall width:  $10.00 \pm 0.20$
- Overall height:  $15.30 \pm 0.30$
- Pin height (from base):  $4.90 \pm 0.20$
- Pin pitch:  $2.54$  TYP
- Pin diameter:  $0.80 \pm 0.10$
- Pin length (from base):  $1.27 \pm 0.10$
- Pin spacing (from center):  $1.40 \pm 0.20$
- Pin diameter (from center):  $1.20 \pm 0.20$
- Pin diameter (from center):  $9.20 \pm 0.20$
- Pin diameter (from center):  $1.20 \pm 0.20$
- Pin diameter (from center):  $0.40$

Package Dimensions (Continued)

I<sup>2</sup>PAK



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